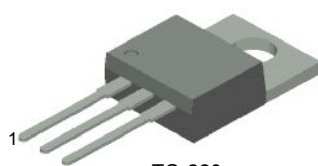


FJP5555

NPN Silicon Transistor

High Voltage Switch Mode Application

- Fast Speed Switching
- Wide Safe Operating Area
- Suitable for Electronic Ballast Application



TO-220

1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings * $T_C=25^{\circ}\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------|------------------------------------|------------|--------------------|
| BV_{CBO} | Collector-Base Voltage | 1050 | V |
| BV_{CEO} | Collector-Emitter Voltage | 400 | V |
| BV_{EBO} | Emitter-Base Voltage | 14 | V |
| I_C | Collector Current (DC) | 5 | A |
| I_{CP} | Collector Current (Pulse) | 10 | A |
| P_C | Collector Dissipation. | 85 | W |
| T_J | Junction Temperature | 150 | $^{\circ}\text{C}$ |
| T_{STG} | Storage Junction Temperature Range | - 55 ~ 150 | $^{\circ}\text{C}$ |

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Ordering Information

| Part Number | Marking | Package | Packing Method | Remarks |
|-------------|---------|---------|----------------|---------|
| FJP5555TU | J5555 | TO220 | TUBE | |

Electrical Characteristics * $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Conditions | Min. | Typ. | Max | Units |
|---------------|--------------------------------------|--|------|------|-----|---------------|
| BV_{CBO} | Collector-Base Breakdown Voltage | $I_C=500\mu\text{A}, I_E=0$ | 1050 | | | V |
| BV_{CEO} | Collector-Emitter Breakdown Voltage | $I_C=5\text{mA}, I_B=0$ | 400 | | | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_E=500\mu\text{A}, I_C=0$ | 14 | | | V |
| h_{FE} | * DC Current Gain | $V_{CE}=5\text{V}, I_C=10\text{mA}$ | 10 | | | |
| | | $V_{CE}=3\text{V}, I_C=0.8\text{A}$ | 20 | | 40 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C=1\text{A}, I_B=0.2\text{A}$ | | | 0.5 | V |
| | | $I_C=3.5\text{A}, I_B=1.0\text{A}$ | | | 1.5 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C=3.5\text{A}, I_B=1.0\text{A}$ | | | 1.2 | V |
| C_{ob} | Output Capacitance | $V_{CB}=10\text{V}, f=1\text{MHz}$ | | 45 | | pF |
| t_{ON} | Turn On Time | $V_{CC}=125\text{V}, I_C=0.5\text{A}$ $I_{B1}=45\text{mA}, I_{B2}=0.5\text{A}$ $R_L=250\Omega$ | | | 1.0 | μs |
| t_{STG} | Storage Time | | | | 1.2 | μs |
| t_F | Fall Time | | | | 0.3 | μs |
| t_{ON} | Turn On Time | $V_{CC}=250\text{V}, I_C=2.5\text{A}$ $I_{B1}=0.5\text{A}, I_{B2}=1.0\text{A}$ $R_L=100\Omega$ | | | 2.0 | μs |
| t_{STG} | Storage Time | | | | 2.5 | μs |
| t_F | Fall Time | | | | 0.3 | μs |
| EAS | Avalanche Energy | $L=2\text{mH}$ | 6 | | | mJ |

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Characteristics

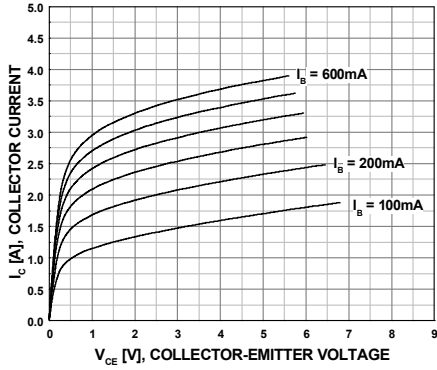


Figure 1. Static Characteristics

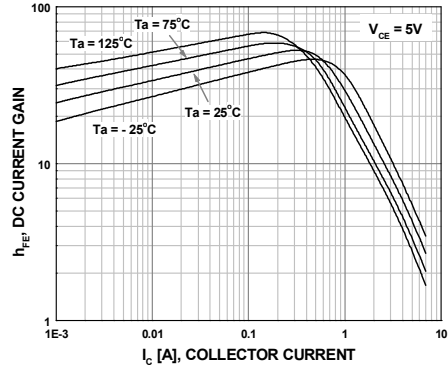


Figure 2. DC Current Gain

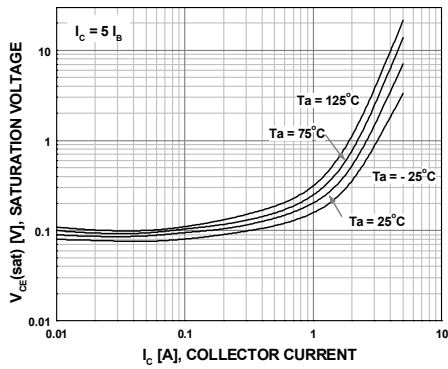


Figure 3. Saturation Voltage

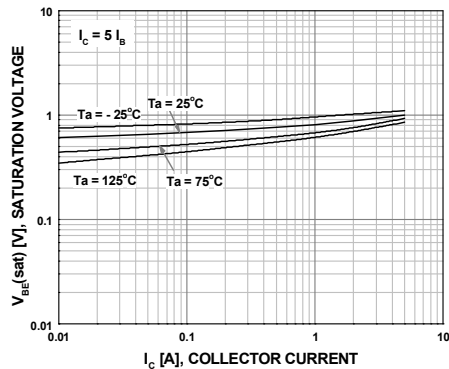


Figure 4. Saturation Voltage

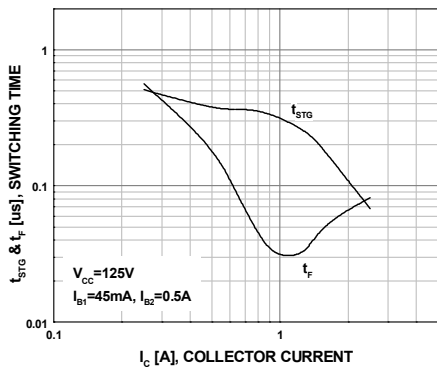


Figure 5. Resistive Load Switching

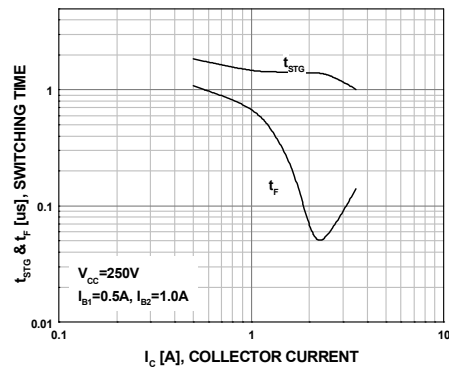


Figure 6. Resistive Load Switching

Typical Characteristics (Continued)

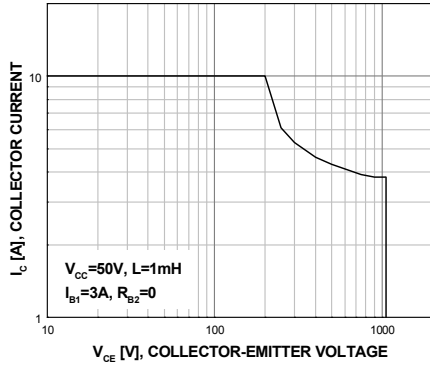


Figure 7. Reverse Biased Safe Operating Area

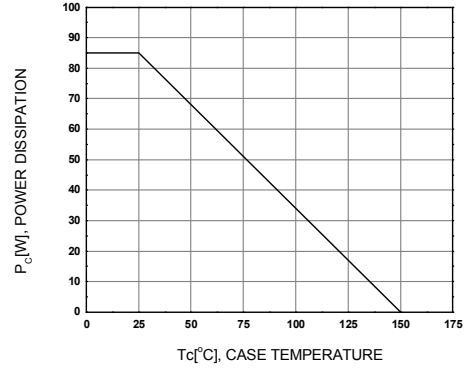


Figure 8. Power Derating

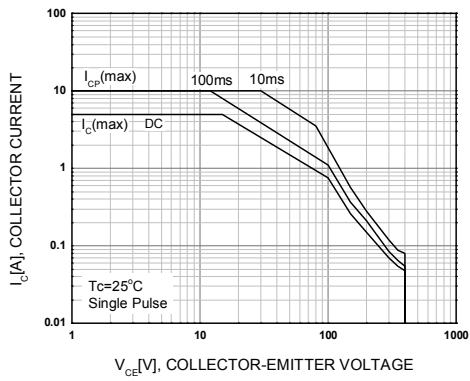
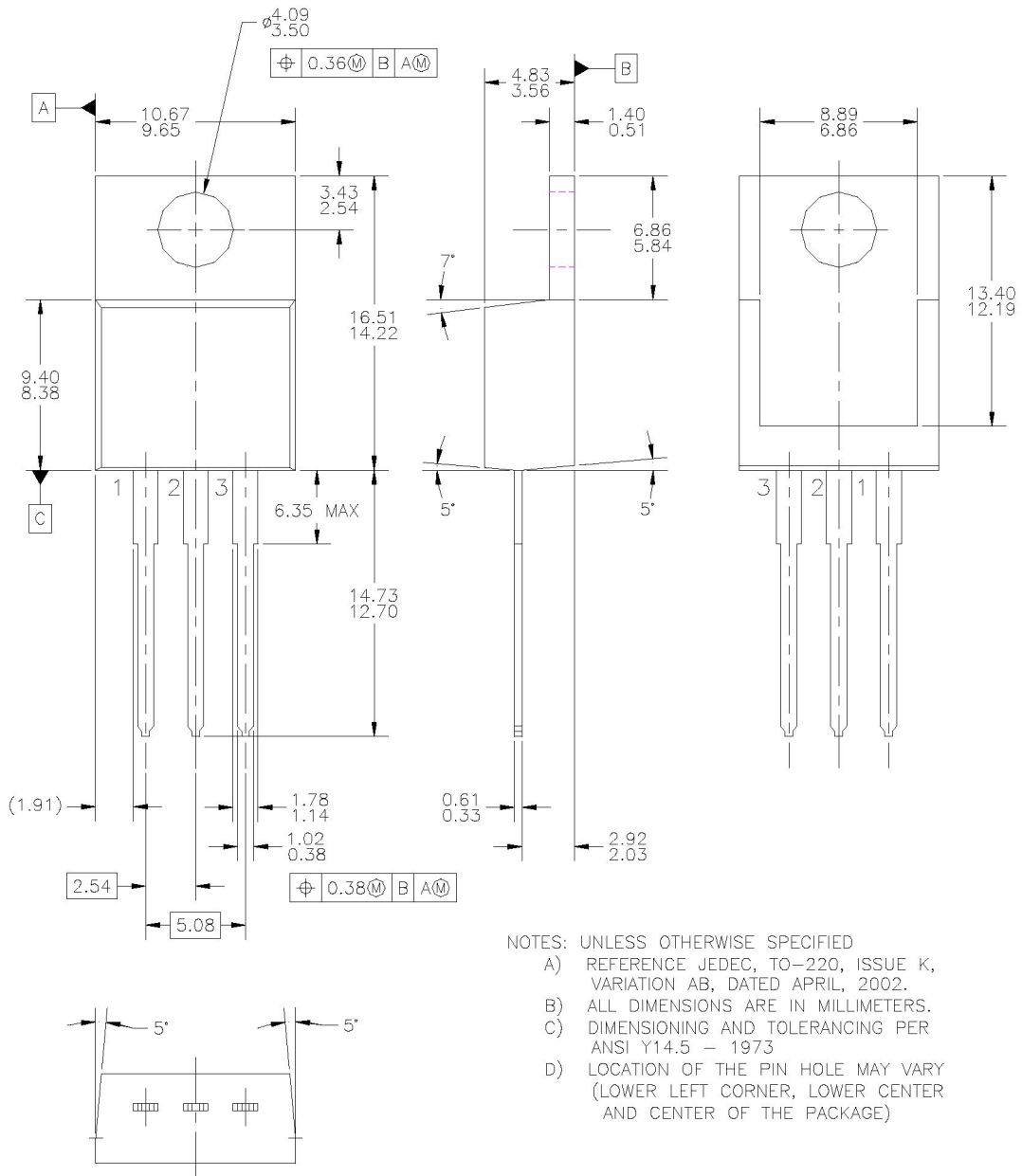


Figure 9. Forward Biased Safe Operating Area

Mechanical Dimensions

TO220





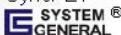


- NOTES: UNLESS OTHERWISE SPECIFIED
- A) REFERENCE JEDEC, TO-220, ISSUE K, VARIATION AB, DATED APRIL, 2002.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5 - 1973
 - D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)



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